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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I ² C, IrDA, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	37
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 10x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l053c8t6

2 Description

The ultra-low-power STM32L053x6/8 microcontrollers incorporate the connectivity power of the universal serial bus (USB 2.0 crystal-less) with the high-performance ARM® Cortex®-M0+ 32-bit RISC core operating at a 32 MHz frequency, a memory protection unit (MPU), high-speed embedded memories (up to 64 Kbytes of Flash program memory, 2 Kbytes of data EEPROM and 8 Kbytes of RAM) plus an extensive range of enhanced I/Os and peripherals.

The STM32L053x6/8 devices provide high power efficiency for a wide range of performance. It is achieved with a large choice of internal and external clock sources, an internal voltage adaptation and several low-power modes.

The STM32L053x6/8 devices offer several analog features, one 12-bit ADC with hardware oversampling, one DAC, two ultra-low-power comparators, several timers, one low-power timer (LPTIM), three general-purpose 16-bit timers and one basic timer, one RTC and one SysTick which can be used as timebases. They also feature two watchdogs, one watchdog with independent clock and window capability and one window watchdog based on bus clock.

Moreover, the STM32L053x6/8 devices embed standard and advanced communication interfaces: up to two I2C, two SPIs, one I2S, two USARTs, a low-power UART (LPUART), and a crystal-less USB. The devices offer up to 24 capacitive sensing channels to simply add touch sensing functionality to any application.

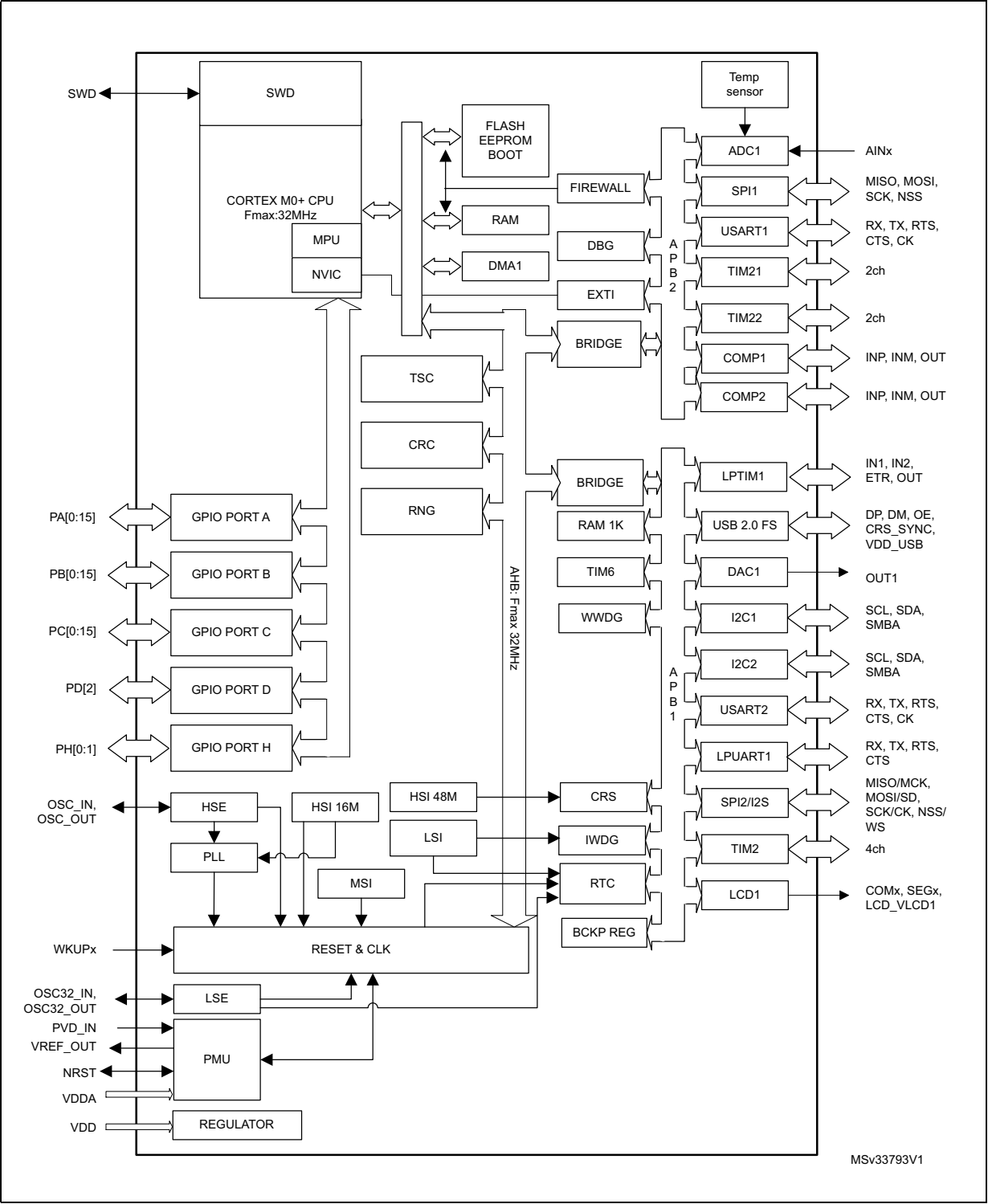
The STM32L053x6/8 also include a real-time clock and a set of backup registers that remain powered in Standby mode.

Finally, their integrated LCD controller has a built-in LCD voltage generator that allows to drive up to 8 multiplexed LCDs with contrast independent of the supply voltage.

The ultra-low-power STM32L053x6/8 devices operate from a 1.8 to 3.6 V power supply (down to 1.65 V at power down) with BOR and from a 1.65 to 3.6 V power supply without BOR option. They are available in the -40 to +125 °C temperature range. A comprehensive set of power-saving modes allows the design of low-power applications.



Figure 1. STM32L053x6/8 block diagram



- **Stop mode without RTC**

The Stop mode achieves the lowest power consumption while retaining the RAM and register contents. All clocks are stopped, the PLL, MSI RC, HSI and LSI RC, HSE and LSE crystal oscillators are disabled.

Some peripherals featuring wakeup capability can enable the HSI RC during Stop mode to detect their wakeup condition.

The voltage regulator is in the low-power mode. The device can be woken up from Stop mode by any of the EXTI line, in 3.5 μ s, the processor can serve the interrupt or resume the code. The EXTI line source can be any GPIO. It can be the PVD output, the comparator 1 event or comparator 2 event (if internal reference voltage is on). It can also be wakened by the USB/USART/I2C/LPUART/LPTIMER wakeup events.

- **Standby mode with RTC**

The Standby mode is used to achieve the lowest power consumption and real time clock. The internal voltage regulator is switched off so that the entire V_{CORE} domain is powered off. The PLL, MSI RC, HSE crystal and HSI RC oscillators are also switched off. The LSE or LSI is still running. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32 KHz oscillator, RCC_CSR register).

The device exits Standby mode in 60 μ s when an external reset (NRST pin), an IWDG reset, a rising edge on one of the three WKUP pins, RTC alarm (Alarm A or Alarm B), RTC tamper event, RTC timestamp event or RTC Wakeup event occurs.

- **Standby mode without RTC**

The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire V_{CORE} domain is powered off. The PLL, MSI RC, HSI and LSI RC, HSE and LSE crystal oscillators are also switched off. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32 KHz oscillator, RCC_CSR register).

The device exits Standby mode in 60 μ s when an external reset (NRST pin) or a rising edge on one of the three WKUP pin occurs.

Note: The RTC, the IWDG, and the corresponding clock sources are not stopped automatically by entering Stop or Standby mode. The LCD is not stopped automatically by entering Stop mode.

3.3 ARM® Cortex®-M0+ core with MPU

The Cortex-M0+ processor is an entry-level 32-bit ARM Cortex processor designed for a broad range of embedded applications. It offers significant benefits to developers, including:

- a simple architecture that is easy to learn and program
- ultra-low power, energy-efficient operation
- excellent code density
- deterministic, high-performance interrupt handling
- upward compatibility with Cortex-M processor family
- platform security robustness, with integrated Memory Protection Unit (MPU).

The Cortex-M0+ processor is built on a highly area and power optimized 32-bit processor core, with a 2-stage pipeline Von Neumann architecture. The processor delivers exceptional energy efficiency through a small but powerful instruction set and extensively optimized design, providing high-end processing hardware including a single-cycle multiplier.

The Cortex-M0+ processor provides the exceptional performance expected of a modern 32-bit architecture, with a higher code density than other 8-bit and 16-bit microcontrollers.

Owing to its embedded ARM core, the STM32L053x6/8 are compatible with all ARM tools and software.

Nested vectored interrupt controller (NVIC)

The ultra-low-power STM32L053x6/8 embed a nested vectored interrupt controller able to handle up to 32 maskable interrupt channels and 4 priority levels.

The Cortex-M0+ processor closely integrates a configurable Nested Vectored Interrupt Controller (NVIC), to deliver industry-leading interrupt performance. The NVIC:

- includes a Non-Maskable Interrupt (NMI)
- provides zero jitter interrupt option
- provides four interrupt priority levels

The tight integration of the processor core and NVIC provides fast execution of Interrupt Service Routines (ISRs), dramatically reducing the interrupt latency. This is achieved through the hardware stacking of registers, and the ability to abandon and restart load-multiple and store-multiple operations. Interrupt handlers do not require any assembler wrapper code, removing any code overhead from the ISRs. Tail-chaining optimization also significantly reduces the overhead when switching from one ISR to another.

To optimize low-power designs, the NVIC integrates with the sleep modes, that include a deep sleep function that enables the entire device to enter rapidly stop or standby mode.

This hardware block provides flexible interrupt management features with minimal interrupt latency.

- **Startup clock**

After reset, the microcontroller restarts by default with an internal 2 MHz clock (MSI). The prescaler ratio and clock source can be changed by the application program as soon as the code execution starts.

- **Clock security system (CSS)**

This feature can be enabled by software. If an HSE clock failure occurs, the master clock is automatically switched to HSI and a software interrupt is generated if enabled. Another clock security system can be enabled, in case of failure of the LSE it provides an interrupt or wakeup event which is generated if enabled.

- **Clock-out capability (MCO: microcontroller clock output)**

It outputs one of the internal clocks for external use by the application.

Several prescalers allow the configuration of the AHB frequency, each APB (APB1 and APB2) domains. The maximum frequency of the AHB and the APB domains is 32 MHz. See [Figure 2](#) for details on the clock tree.

3.13.2 V_{LCD} voltage monitoring

This embedded hardware feature allows the application to measure the V_{LCD} supply voltage using the internal ADC channel ADC_IN16. As the V_{LCD} voltage may be higher than V_{DDA} , and thus outside the ADC input range, the ADC input is connected to LCD_VLCD2 (which provides $1/3V_{LCD}$ when the LCD is configured 1/3Bias and $1/4V_{LCD}$ when the LCD is configured 1/4Bias or 1/2Bias).

3.14 Digital-to-analog converter (DAC)

One 12-bit buffered DAC can be used to convert digital signal into analog voltage signal output. An optional amplifier can be used to reduce the output signal impedance.

This digital Interface supports the following features:

- One data holding register
- Left or right data alignment in 12-bit mode
- Synchronized update capability
- Noise-wave generation
- Triangular-wave generation
- DMA capability (including the underrun interrupt)
- External triggers for conversion
- Input reference voltage V_{REF+}

Four DAC trigger inputs are used in the STM32L053x6/8. The DAC channel is triggered through the timer update outputs that are also connected to different DMA channels.

3.15 Ultra-low-power comparators and reference voltage

The STM32L053x6/8 embed two comparators sharing the same current bias and reference voltage. The reference voltage can be internal or external (coming from an I/O).

- One comparator with ultra low consumption
- One comparator with rail-to-rail inputs, fast or slow mode.
- The threshold can be one of the following:
 - DAC output
 - External I/O pins
 - Internal reference voltage (V_{REFINT})
 - submultiple of Internal reference voltage (1/4, 1/2, 3/4) for the rail to rail comparator.

Both comparators can wake up the devices from Stop mode, and be combined into a window comparator.

The internal reference voltage is available externally via a low-power / low-current output buffer (driving current capability of 1 μ A typical).

Table 8. Capacitive sensing GPIOs available on STM32L053x6/8 devices

Group	Capacitive sensing signal name	Pin name	Group	Capacitive sensing signal name	Pin name
4	TSC_G4_IO1	PA9	8	TSC_G8_IO1	PC6
	TSC_G4_IO2	PA10		TSC_G8_IO2	PC7
	TSC_G4_IO3	PA11		TSC_G8_IO3	PC8
	TSC_G4_IO4	PA12		TSC_G8_IO4	PC9

1. This GPIO offers a reduced touch sensing sensitivity. It is thus recommended to use it as sampling capacitor I/O.

3.18 Timers and watchdogs

The ultra-low-power STM32L053x6/8 devices include three general-purpose timers, one low-power timer (LPTIM), one basic timer, two watchdog timers and the SysTick timer.

[Table 9](#) compares the features of the general-purpose and basic timers.

Table 9. Timer feature comparison

Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary outputs
TIM2	16-bit	Up, down, up/down	Any integer between 1 and 65536	Yes	4	No
TIM21, TIM22	16-bit	Up, down, up/down	Any integer between 1 and 65536	No	2	No
TIM6	16-bit	Up	Any integer between 1 and 65536	Yes	0	No

3.18.1 General-purpose timers (TIM2, TIM21 and TIM22)

There are three synchronizable general-purpose timers embedded in the STM32L053x6/8 devices (see [Table 9](#) for differences).

TIM2

TIM2 is based on 16-bit auto-reload up/down counter. It includes a 16-bit prescaler. It features four independent channels each for input capture/output compare, PWM or one-pulse mode output.

The TIM2 general-purpose timers can work together or with the TIM21 and TIM22 general-purpose timers via the Timer Link feature for synchronization or event chaining. Their counter can be frozen in debug mode. Any of the general-purpose timers can be used to generate PWM outputs.

TIM2 has independent DMA request generation.

This timer is capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 3 hall-effect sensors.

6.3 Operating conditions

6.3.1 General operating conditions

Table 24. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f _{HCLK}	Internal AHB clock frequency	-	0	32	MHz
f _{PCLK1}	Internal APB1 clock frequency	-	0	32	
f _{PCLK2}	Internal APB2 clock frequency	-	0	32	
V _{DD}	Standard operating voltage	BOR detector disabled	1.65	3.6	V
		BOR detector enabled, at power-on	1.8	3.6	
		BOR detector disabled, after power-on	1.65	3.6	
V _{DDA}	Analog operating voltage (DAC not used)	Must be the same voltage as V _{DD} ⁽¹⁾	1.65	3.6	V
V _{DDA}	Analog operating voltage (all features)	Must be the same voltage as V _{DD} ⁽¹⁾	1.8	3.6	V
V _{DD_USB} B	Standard operating voltage, USB domain ⁽²⁾	USB peripheral used	3.0	3.6	V
		USB peripheral not used	1.65	3.6	
V _{IN}	Input voltage on FT, FTf and RST pins ⁽³⁾	2.0 V ≤ V _{DD} ≤ 3.6 V	-0.3	5.5	V
		1.65 V ≤ V _{DD} ≤ 2.0 V	-0.3	5.2	
	Input voltage on BOOT0 pin	-	0	5.5	
	Input voltage on TC pin	-	-0.3	V _{DD} +0.3	
P _D	Power dissipation at T _A = 85 °C (range 6) or T _A = 105 °C (range 7) ⁽⁴⁾	TFBGA64 package	-	327	mW
		LQFP64 package	-	444	
		LQFP48 package	-	363	
	Power dissipation at T _A = 125 °C (range 3) ⁽⁴⁾	TFBGA64 package	-	81	
		LQFP64 package	-	111	
		LQFP48 package	-	91	
T _A	Temperature range	Maximum power dissipation (range 6)	-40	85	°C
		Maximum power dissipation (range 7)	-40	105	
		Maximum power dissipation (range 3)	-40	125	
T _J	Junction temperature range (range 6)	-40 °C ≤ T _A ≤ 85 °	-40	105	
	Junction temperature range (range 7)	-40 °C ≤ T _A ≤ 105 °C	-40	125	
	Junction temperature range (range 3)	-40 °C ≤ T _A ≤ 125 °C	-40	130	

1. It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and normal operation.

Table 28. Current consumption in Run mode, code with data processing running from Flash

Symbol	Parameter	Conditions		f _{HCLK}	Typ	Max ⁽¹⁾	Unit
I _{DD} (Run from Flash)	Supply current in Run mode, code executed from Flash	f _{HSE} = f _{HCLK} up to 16 MHz included, f _{HSE} = f _{HCLK} /2 above 16 MHz (PLL ON) ⁽²⁾	Range 3, V _{CORE} =1.2 V VOS[1:0]=11	1 MHz	165	230	μA
				2 MHz	290	360	
				4 MHz	555	630	
			Range 2, V _{CORE} =1.5 V, VOS[1:0]=10,	4 MHz	0.665	0.74	mA
				8 MHz	1.3	1.4	
				16 MHz	2.6	2.8	
			Range 1, V _{CORE} =1.8 V, VOS[1:0]=01	8 MHz	1.55	1.7	
				16 MHz	3.1	3.4	
				32 MHz	6.3	6.8	
		MSI clock	Range 3, V _{CORE} =1.2 V, VOS[1:0]=11	65 kHz	36.5	110	μA
				524 kHz	99.5	190	
				4.2 MHz	620	700	
		HSI clock	Range 2, V _{CORE} =1.5 V, VOS[1:0]=10,	16 MHz	2.6	2.9	mA
			Range 1, V _{CORE} =1.8 V, VOS[1:0]=01	32 MHz	6.25	7	

1. Guaranteed by characterization results at 125 °C, unless otherwise specified.

2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Table 29. Current consumption in Run mode vs code type,
code with data processing running from Flash

Symbol	Parameter	Conditions			f _{HCLK}	Typ	Unit
I _{DD} (Run from Flash)	Supply current in Run mode, code executed from Flash	f _{HSE} = f _{HCLK} up to 16 MHz included, f _{HSE} = f _{HCLK} /2 above 16 MHz (PLL ON) ⁽¹⁾	Range 3, V _{CORE} =1.2 V, VOS[1:0]=11	Dhrystone	4 MHz	555	μA
				CoreMark		585	
				Fibonacci		440	
				while(1)		355	
				while(1), prefetch OFF		353	
			Range 1, V _{CORE} =1.8 V, VOS[1:0]=01	Dhrystone	32 MHz	6.3	mA
				CoreMark		6.3	
				Fibonacci		6.55	
				while(1)		5.4	
				while(1), prefetch OFF		5.2	

1. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Table 39. Peripheral current consumption in Stop and Standby mode⁽¹⁾

Symbol	Peripheral	Typical consumption, T _A = 25 °C		Unit
		V _{DD} =1.8 V	V _{DD} =3.0 V	
I _{DD} (PVD / BOR)	-	0.7	1.2	μA
I _{REFINT}	-	-	1.4	
-	LSE Low drive ⁽²⁾	0,1	0,1	
-	LPTIM1, Input 100 Hz	0,01	0,01	
-	LPTIM1, Input 1 MHz	6	6	
-	LPUART1	0,2	0,2	
-	RTC	0,3	0,48	μA
-	LCD1 (static duty)	0,15	0,15	
-	LCD1 (1/8 duty)	1,6	2,6	

1. LPTIM peripheral cannot operate in Standby mode.

2. LSE Low drive consumption is the difference between an external clock on OSC32_IN and a quartz between OSC32_IN and OSC32_OUT.-

6.3.5 Wakeup time from low-power mode

The wakeup times given in the following table are measured with the MSI or HSI16 RC oscillator. The clock source used to wake up the device depends on the current operating mode:

- Sleep mode: the clock source is the clock that was set before entering Sleep mode
- Stop mode: the clock source is either the MSI oscillator in the range configured before entering Stop mode, the HSI16 or HSI16/4.
- Standby mode: the clock source is the MSI oscillator running at 2.1 MHz

All timings are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 24](#).

High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 1 to 25 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in [Table 43](#). In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

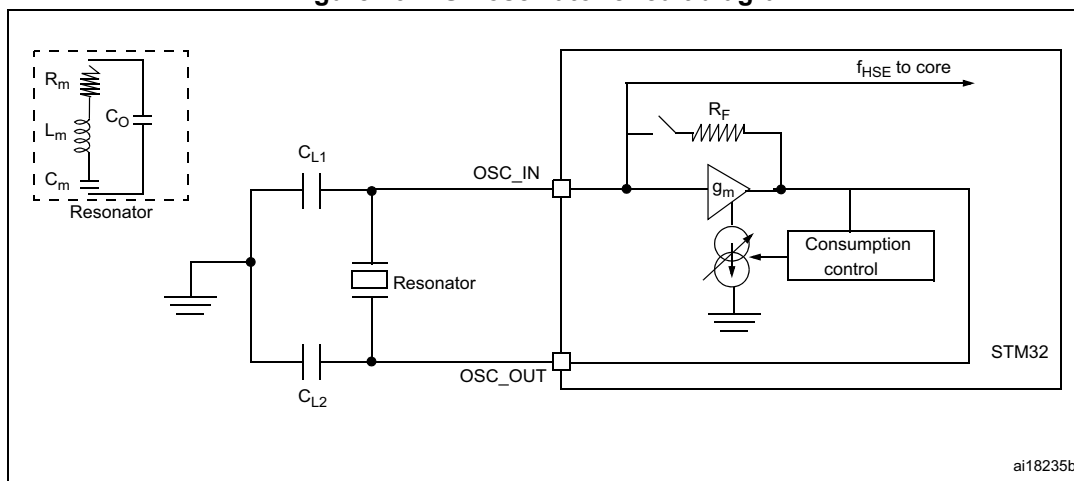
Table 43. HSE oscillator characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{OSC_IN}	Oscillator frequency	-	1		25	MHz
R_F	Feedback resistor	-	-	200	-	k Ω
G_m	Maximum critical crystal transconductance	Startup	-	-	700	$\mu A/V$
$t_{SU(HSE)}^{(2)}$	Startup time	V_{DD} is stabilized	-	2	-	ms

1. Guaranteed by design.
2. Guaranteed by characterization results. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

For C_{L1} and C_{L2} , it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see [Figure 19](#)). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2} . Refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Figure 19. HSE oscillator circuit diagram



Output voltage levels

Unless otherwise specified, the parameters given in [Table 59](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 24](#). All I/Os are CMOS and TTL compliant.

Table 59. Output voltage characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{OL}^{(1)}$	Output low level voltage for an I/O pin	CMOS port ⁽²⁾ , $I_{IO} = +8 \text{ mA}$ $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	-	0.4	V
$V_{OH}^{(3)}$	Output high level voltage for an I/O pin		$V_{DD}-0.4$	-	
$V_{OL}^{(1)}$	Output low level voltage for an I/O pin	TTL port ⁽²⁾ , $I_{IO} = +8 \text{ mA}$ $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	-	0.4	
$V_{OH}^{(3)(4)}$	Output high level voltage for an I/O pin	TTL port ⁽²⁾ , $I_{IO} = -6 \text{ mA}$ $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	2.4	-	
$V_{OL}^{(1)(4)}$	Output low level voltage for an I/O pin	$I_{IO} = +15 \text{ mA}$ $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	-	1.3	
$V_{OH}^{(3)(4)}$	Output high level voltage for an I/O pin	$I_{IO} = -15 \text{ mA}$ $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	$V_{DD}-1.3$	-	
$V_{OL}^{(1)(4)}$	Output low level voltage for an I/O pin	$I_{IO} = +4 \text{ mA}$ $1.65 \text{ V} \leq V_{DD} < 3.6 \text{ V}$	-	0.45	
$V_{OH}^{(3)(4)}$	Output high level voltage for an I/O pin	$I_{IO} = -4 \text{ mA}$ $1.65 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	$V_{DD}-0.45$	-	
$V_{OLFM+}^{(1)(4)}$	Output low level voltage for an FTf I/O pin in Fm+ mode	$I_{IO} = 20 \text{ mA}$ $2.7 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	-	0.4	
		$I_{IO} = 10 \text{ mA}$ $1.65 \text{ V} \leq V_{DD} \leq 3.6 \text{ V}$	-	0.4	

1. The I_{IO} current sunk by the device must always respect the absolute maximum rating specified in [Table 22](#). The sum of the currents sunk by all the I/Os (I/O ports and control pins) must always be respected and must not exceed $\Sigma I_{IO(PIN)}$.
2. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.
3. The I_{IO} current sourced by the device must always respect the absolute maximum rating specified in [Table 22](#). The sum of the currents sourced by all the I/Os (I/O ports and control pins) must always be respected and must not exceed $\Sigma I_{IO(PIN)}$.
4. Guaranteed by characterization results.

Input/output AC characteristics

The definition and values of input/output AC characteristics are given in [Figure 24](#) and [Table 60](#), respectively.

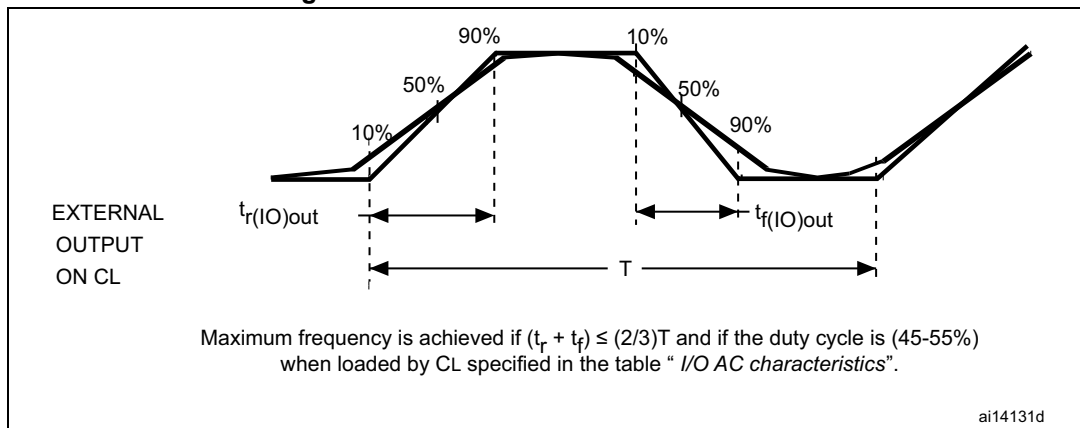
Unless otherwise specified, the parameters given in [Table 60](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 24](#).

Table 60. I/O AC characteristics⁽¹⁾

OSPEEDRx[1:0] bit value ⁽¹⁾	Symbol	Parameter	Conditions	Min	Max ⁽²⁾	Unit
00	$f_{\max(\text{IO})\text{out}}$	Maximum frequency ⁽³⁾	$C_L = 50 \text{ pF}$, $V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	400	kHz
			$C_L = 50 \text{ pF}$, $V_{DD} = 1.65 \text{ V to } 2.7 \text{ V}$	-	100	
	$t_{f(\text{IO})\text{out}}$ $t_{r(\text{IO})\text{out}}$	Output rise and fall time	$C_L = 50 \text{ pF}$, $V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	125	ns
			$C_L = 50 \text{ pF}$, $V_{DD} = 1.65 \text{ V to } 2.7 \text{ V}$	-	320	
01	$f_{\max(\text{IO})\text{out}}$	Maximum frequency ⁽³⁾	$C_L = 50 \text{ pF}$, $V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	2	MHz
			$C_L = 50 \text{ pF}$, $V_{DD} = 1.65 \text{ V to } 2.7 \text{ V}$	-	0.6	
	$t_{f(\text{IO})\text{out}}$ $t_{r(\text{IO})\text{out}}$	Output rise and fall time	$C_L = 50 \text{ pF}$, $V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	30	ns
			$C_L = 50 \text{ pF}$, $V_{DD} = 1.65 \text{ V to } 2.7 \text{ V}$	-	65	
10	$F_{\max(\text{IO})\text{out}}$	Maximum frequency ⁽³⁾	$C_L = 50 \text{ pF}$, $V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	10	MHz
			$C_L = 50 \text{ pF}$, $V_{DD} = 1.65 \text{ V to } 2.7 \text{ V}$	-	2	
	$t_{f(\text{IO})\text{out}}$ $t_{r(\text{IO})\text{out}}$	Output rise and fall time	$C_L = 50 \text{ pF}$, $V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	13	ns
			$C_L = 50 \text{ pF}$, $V_{DD} = 1.65 \text{ V to } 2.7 \text{ V}$	-	28	
11	$F_{\max(\text{IO})\text{out}}$	Maximum frequency ⁽³⁾	$C_L = 30 \text{ pF}$, $V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	35	MHz
			$C_L = 50 \text{ pF}$, $V_{DD} = 1.65 \text{ V to } 2.7 \text{ V}$	-	10	
	$t_{f(\text{IO})\text{out}}$ $t_{r(\text{IO})\text{out}}$	Output rise and fall time	$C_L = 30 \text{ pF}$, $V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	6	ns
			$C_L = 50 \text{ pF}$, $V_{DD} = 1.65 \text{ V to } 2.7 \text{ V}$	-	17	
Fm+ configuration ⁽⁴⁾	$f_{\max(\text{IO})\text{out}}$	Maximum frequency ⁽³⁾	$C_L = 50 \text{ pF}$, $V_{DD} = 2.5 \text{ V to } 3.6 \text{ V}$	-	1	MHz
	$t_{f(\text{IO})\text{out}}$	Output fall time		-	10	ns
	$t_{r(\text{IO})\text{out}}$	Output rise time		-	30	
	$f_{\max(\text{IO})\text{out}}$	Maximum frequency ⁽³⁾	$C_L = 50 \text{ pF}$, $V_{DD} = 1.65 \text{ V to } 3.6 \text{ V}$	-	350	KHz
	$t_{f(\text{IO})\text{out}}$	Output fall time		-	15	ns
	$t_{r(\text{IO})\text{out}}$	Output rise time		-	60	
-	$t_{\text{EXTI}pw}$	Pulse width of external signals detected by the EXTI controller	-	8	-	ns

1. The I/O speed is configured using the OSPEEDRx[1:0] bits. Refer to the line reference manual for a description of GPIO Port configuration register.
2. Guaranteed by design.
3. The maximum frequency is defined in [Figure 24](#).
4. When Fm+ configuration is set, the I/O speed control is bypassed. Refer to the line reference manual for a detailed description of Fm+ I/O configuration.

Figure 24. I/O AC characteristics definition



6.3.14 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} , except when it is internally driven low (see [Table 61](#)).

Unless otherwise specified, the parameters given in [Table 61](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 24](#).

Table 61. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{IL(NRST)}^{(1)}$	NRST input low level voltage	-	V_{SS}	-	0.8	V
$V_{IH(NRST)}^{(1)}$	NRST input high level voltage	-	1.4	-	V_{DD}	
$V_{OL(NRST)}^{(1)}$	NRST output low level voltage	$I_{OL} = 2 \text{ mA}$ $2.7 \text{ V} < V_{DD} < 3.6 \text{ V}$	-	-	0.4	
		$I_{OL} = 1.5 \text{ mA}$ $1.65 \text{ V} < V_{DD} < 2.7 \text{ V}$	-	-		
$V_{hys(NRST)}^{(1)}$	NRST Schmitt trigger voltage hysteresis	-	-	$10\%V_{DD}^{(2)}$	-	mV
R_{PU}	Weak pull-up equivalent resistor ⁽³⁾	$V_{IN} = V_{SS}$	30	45	60	kΩ
$V_{F(NRST)}^{(1)}$	NRST input filtered pulse	-	-	-	50	ns
$V_{NF(NRST)}^{(1)}$	NRST input not filtered pulse	-	350	-	-	ns

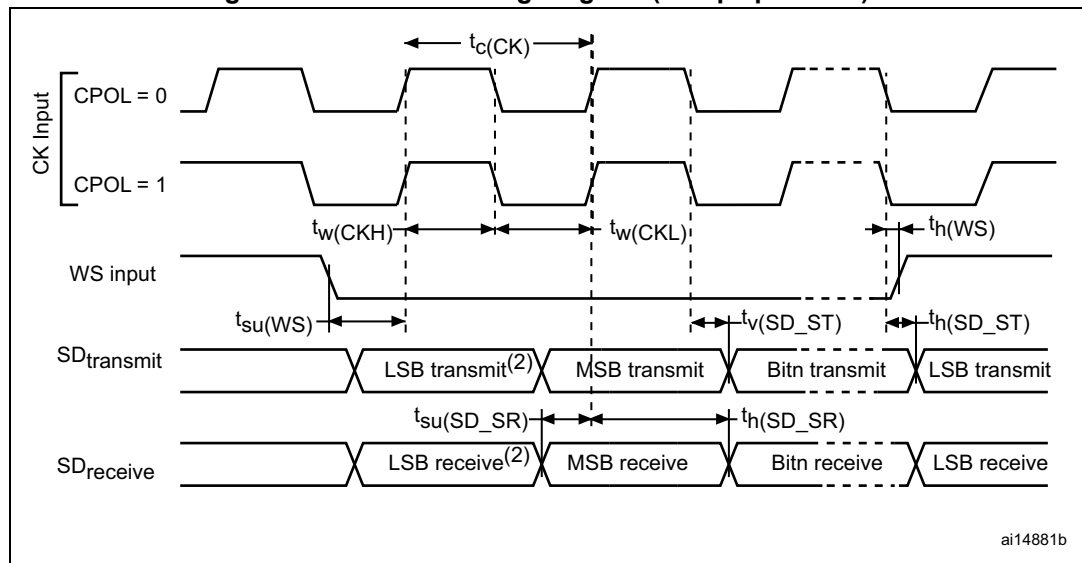
1. Guaranteed by design.

2. 200 mV minimum value

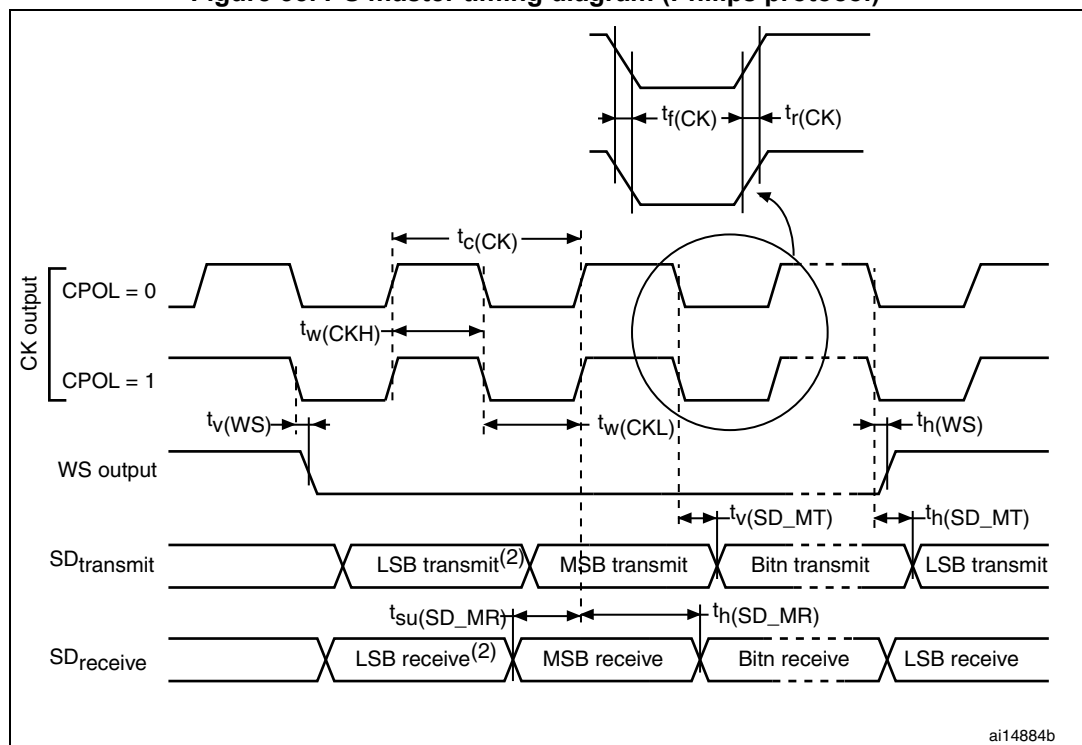
3. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is around 10%.

Table 65. DAC characteristics (continued)

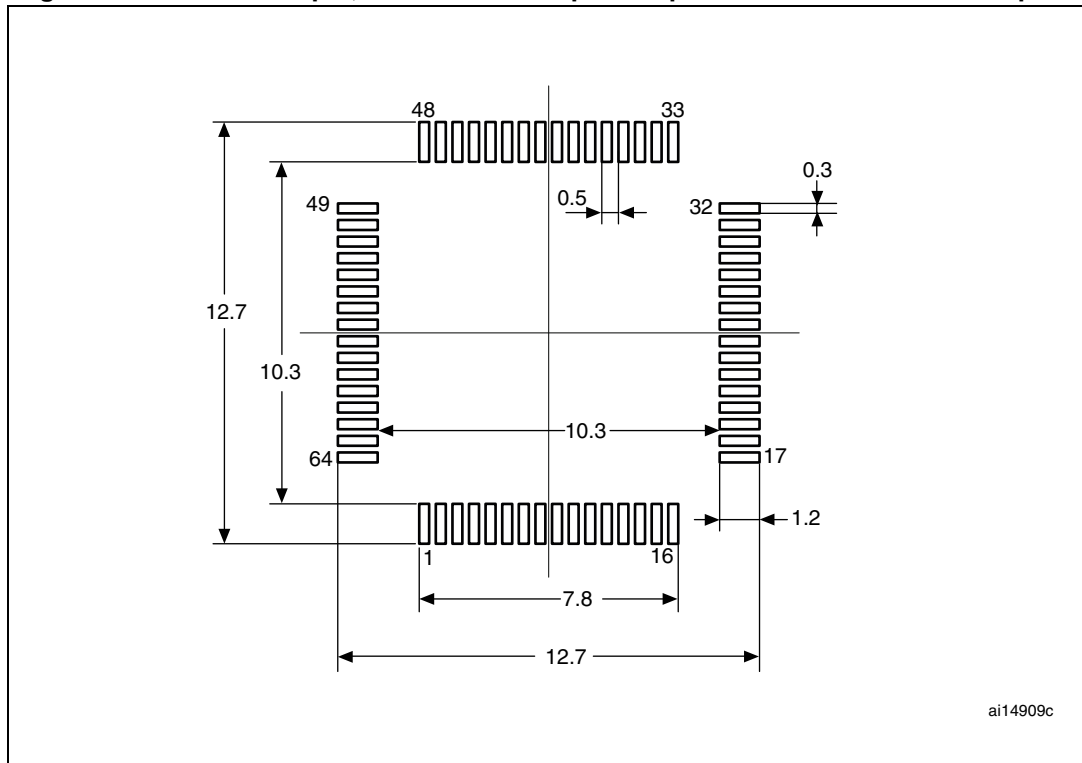
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
DNL ⁽²⁾	Differential non linearity ⁽⁴⁾	$C_L \leq 50$ pF, $R_L \geq 5$ k Ω DAC output buffer ON	-	1.5	3	LSB
		No R_{LOAD} , $C_L \leq 50$ pF DAC output buffer OFF	-	1.5	3	
INL ⁽²⁾	Integral non linearity ⁽⁵⁾	$C_L \leq 50$ pF, $R_L \geq 5$ k Ω DAC output buffer ON	-	2	4	
		No R_{LOAD} , $C_L \leq 50$ pF DAC output buffer OFF	-	2	4	
Offset ⁽²⁾	Offset error at code 0x800 ⁽⁶⁾	$C_L \leq 50$ pF, $R_L \geq 5$ k Ω DAC output buffer ON	-	± 10	± 25	
		No R_{LOAD} , $C_L \leq 50$ pF DAC output buffer OFF	-	± 5	± 8	
Offset1 ⁽²⁾	Offset error at code 0x001 ⁽⁷⁾	No R_{LOAD} , $C_L \leq 50$ pF DAC output buffer OFF	-	± 1.5	± 5	
dOffset/dT ⁽²⁾	Offset error temperature coefficient (code 0x800)	$V_{DDA} = 3.3$ V $V_{REF+} = 3.0$ V $T_A = 0$ to 50 °C DAC output buffer OFF	-20	-10	0	$\mu V/^{\circ}C$
		$V_{DDA} = 3.3$ V $V_{REF+} = 3.0$ V $T_A = 0$ to 50 °C DAC output buffer ON	0	20	50	
Gain ⁽²⁾	Gain error ⁽⁸⁾	$C_L \leq 50$ pF, $R_L \geq 5$ k Ω DAC output buffer ON	-	+0.1 / -0.2%	+0.2 / -0.5%	%
		No R_{LOAD} , $C_L \leq 50$ pF DAC output buffer OFF	-	+0 / -0.2%	+0 / -0.4%	
dGain/dT ⁽²⁾	Gain error temperature coefficient	$V_{DDA} = 3.3$ V $V_{REF+} = 3.0$ V $T_A = 0$ to 50 °C DAC output buffer OFF	-10	-2	0	$\mu V/^{\circ}C$
		$V_{DDA} = 3.3$ V $V_{REF+} = 3.0$ V $T_A = 0$ to 50 °C DAC output buffer ON	-40	-8	0	
TUE ⁽²⁾	Total unadjusted error	$C_L \leq 50$ pF, $R_L \geq 5$ k Ω DAC output buffer ON	-	12	30	LSB
		No R_{LOAD} , $C_L \leq 50$ pF DAC output buffer OFF	-	8	12	

Figure 34. I²S slave timing diagram (Philips protocol)⁽¹⁾

1. Measurement points are done at CMOS levels: $0.3 \times V_{DD}$ and $0.7 \times V_{DD}$.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Figure 35. I²S master timing diagram (Philips protocol)⁽¹⁾

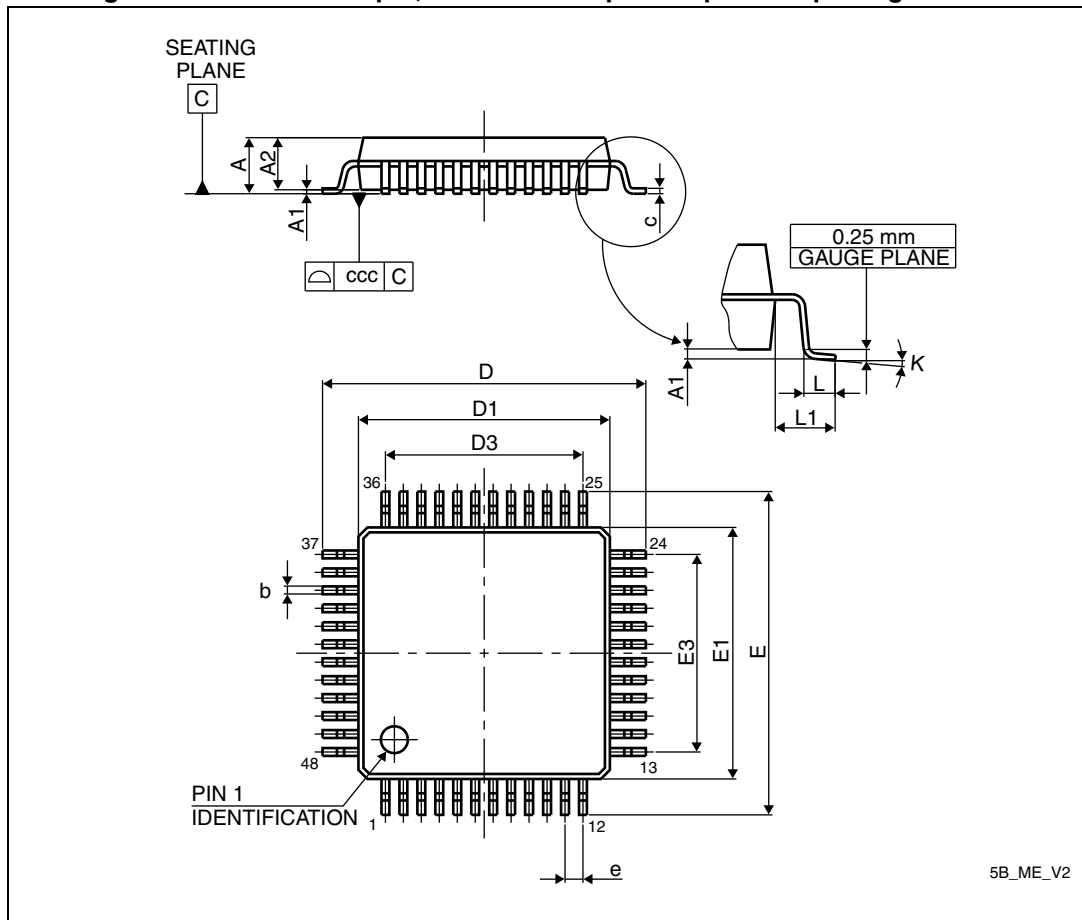
1. Guaranteed by characterization results.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Figure 38. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat recommended footprint

1. Dimensions are expressed in millimeters.

7.3 LQFP48 package information

Figure 43. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package outline



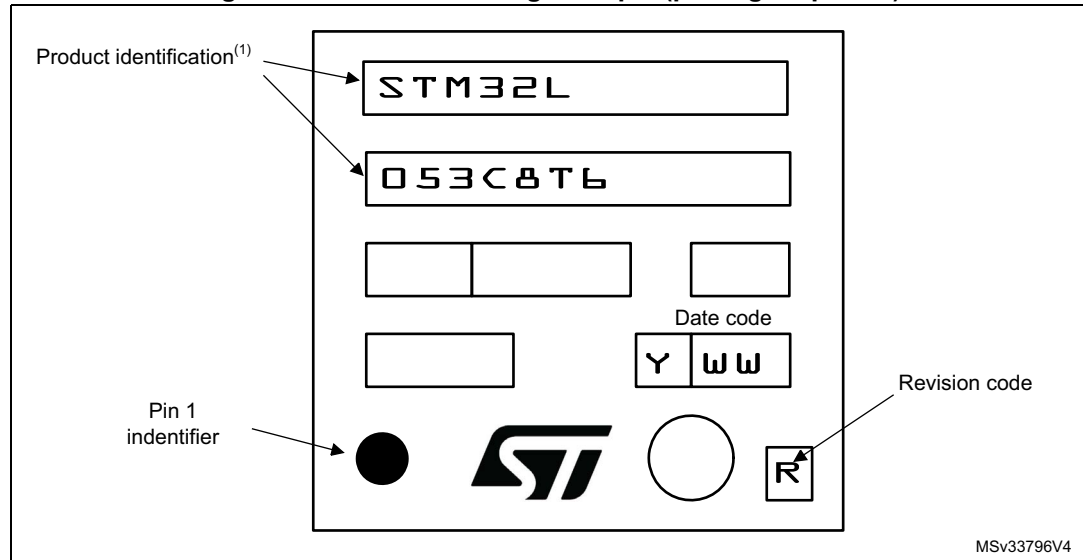
1. Drawing is not to scale.

Device marking for LQFP48

The following figure gives an example of topside marking versus pin 1 position identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

Figure 45. LQFP48 marking example (package top view)



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

Table 87. Document revision history (continued)

Date	Revision	Changes
05-Sep-2014	4	<p>Extended operating temperature range to 125 °C.</p> <p>Updated minimum ADC operating voltage to 1.65 V.</p> <p>Replaced USART3 by LPUART1 in Table 15: STM32L053x6/8 pin definitions and LPUART by LPUART1 in Table 16: Alternate function port A, Table 17: Alternate function port B, Table 18: Alternate function port C, Table 19: Alternate function port D and Table 20: Alternate function port H. Updated PA6 in Table 16: Alternate function port A.</p> <p>Updated temperature range in Section 2: Description, Table 1: Ultra-low-power STM32L053x6/x8 device features and peripheral counts.</p> <p>Updated P_D, T_A and T_J to add range 3 in Table 24: General operating conditions. Added range 3 in Table 51: Flash memory and data EEPROM characteristics, Table 52: Flash memory and data EEPROM endurance and retention. Update note 1 in Table 28: Current consumption in Run mode, code with data processing running from Flash, Table 30: Current consumption in Run mode, code with data processing running from RAM, Table 32: Current consumption in Sleep mode, Table 33: Current consumption in Low-power run mode, Table 34: Current consumption in Low-power sleep mode, Table 35: Typical and maximum current consumptions in Stop mode, Table 36: Typical and maximum current consumptions in Standby mode and Table 40: Low-power mode wakeup timings. Updated Figure 46: Thermal resistance and removed note 1. Updated Figure 14: IDD vs VDD, at TA= 25/55/ 85/105/125 °C, Low-power run mode, code running from RAM, Range 3, MSI (Range 0) at 64 KHz, 0 WS, Figure 15: IDD vs VDD, at TA= 25/55/ 85/105/125 °C, Stop mode with RTC enabled and running on LSE Low drive, Figure 16: IDD vs VDD, at TA= 25/55/85/105/125 °C, Stop mode with RTC disabled, all clocks OFF.</p> <p>Updated Table 36: Typical and maximum current consumptions in Standby mode.</p> <p>Updated SYSCFG in Table 38: Peripheral current consumption in Run or Sleep mode.</p> <p>Updated Table 39: Peripheral current consumption in Stop and Standby mode and Table 40: Low-power mode wakeup timings.</p> <p>Updated ACC_{HSI16} temperature conditions in Table 45: 16 MHz HSI16 oscillator characteristics. Changed ambient temperature range in note 1 below Table 46: HSI48 oscillator characteristics.</p> <p>Updated $V_{F(NRST)}$ and $V_{NF(NRST)}$ in Table 61: NRST pin characteristics.</p> <p>Updated Table 62: ADC characteristics and Table 64: ADC accuracy.</p> <p>Added range 3 in Table 86: STM32L053x6/8 ordering information scheme.</p>